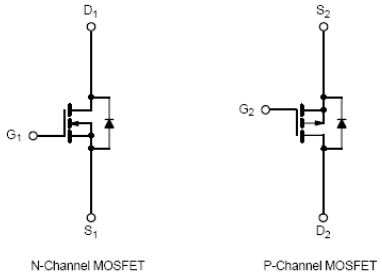
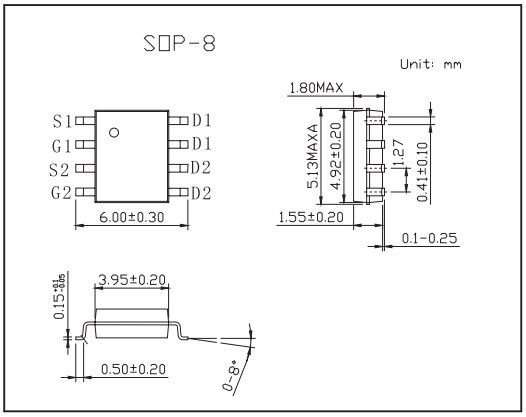
N- and P-Channel 30-V (D-S) MOSFET

KI4532DY

■ PIN Configuration



N-Channel MOSFET P-Channel MOSFET



■ Absolute Maximum Ratings T_A = 25℃

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	±20	±20	V
Continuous Drain Current (T_J = 150℃)* T_A = 25℃	I_D	±3.9	±3.5	A
T_A = 70℃		±3.1	±2.8	A
Pulsed Drain Current	I_{DM}	±20	±20	A
Continuous Source Current (Diode Conduction)*	I_S	1.7	-1.7	A
Maximum Power Dissipation* T_A = 25℃	P_D	2	2	W
T_A = 70℃		1.3	1.3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		℃
Maximum Junction-to-Ambient*	R_{thJA}	62.5		℃/W

*Surface Mounted on FR4 Board, t≤10 sec.

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■ Electrical Characteristics T_J = 25℃

Parameter	Symbol	Testconditons		Min	Typ	Max	Unit
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	N-Ch	1			V
		V_{DS} = V_{GS}, I_D = -250 μA	P-Ch	-1			
Gate Body Leakage	I_{GSS}	V_{DS} = 0 V V_{GS} = ±20 V	N-Ch			±100	nA
		V_{DS} = 0 V V_{GS} = ±20 V	P-Ch			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0 V	N-Ch			1	
		V_{DS} = -30V, V_{GS} = 0 V	P-Ch			-1	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55℃	N-Ch			25	μA
		V_{DS} = -30V, V_{GS} = 0 V, T_J = 55℃	P-Ch			-25	
On State Drain Currenta	$I_{D(on)}$	V_{DS} ≥5 V, V_{GS} = 10 V	N-Ch	15			A
		V_{DS} ≤-5 V, V_{GS} = -10 V	P-Ch	-15			
Drain Source On State Resistance*	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 3.9A	N-Ch		0.043	0.065	Ω
		V_{GS} = -10 V, I_D = -2.5A	P-Ch		0.066	0.085	
		V_{GS} = 4.5 V, I_D = 3.1A	N-Ch		0.075	0.095	
		V_{GS} = -4.5 V, I_D = -1.8A	P-Ch		0.125	0.19	
Forward Transconductance*	g_{fs}	V_{DS} = 15 V, I_D = 3.9A	N-Ch		7		S
		V_{DS} = -15 V, I_D = -2.5A	P-Ch		5		
Diode Forward Voltage*	V_{SD}	I_S = 1.7A, V_{GS} = 0 V	N-Ch		0.8	1.2	V
		I_S = -1.7A, V_{GS} = 0 V	P-Ch		-0.8	-1.2	
Total Gate Charge	Q_g	N-Channel	N-Ch		9.8	15	nC
		V_{DS} = 10 V, V_{GS} = 10V, I_D = 3.9A	P-Ch		8.7	15	
Gate Source Charge	Q_{gs}		N-Ch		2.1		
		P-Channel	P-Ch		1.9		
Gate Drain Charge	Q_{gd}	V_{DS} = -10 V, V_{GS} = -10 V, I_D = -2.5A	N-Ch		1.6		
			P-Ch		1.3		
Turn On Time	$t_{d(on)}$	N Channel	N-Ch		9	15	ns
		V_{DD} = 10 V, R_L = 10Ω	P-Ch		7	15	
Rise Time	t_r	I_D= 1A, V_{GEN} = 10V, R_g = 6 Ω	N-Ch		6	18	
			P-Ch		9	18	
Turn Off Delay Time	$t_{d(off)}$	P-Channel	N-Ch		18	27	
		V_{DD} = -10 V, R_L = 10Ω	P-Ch		14	27	
Fall Time	t_f	I_D= -1 A, V_{GEN} = -10 V, R_g = 6 Ω	N-Ch		6	15	
			P-Ch		8	15	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, di/dt = 100 A/μs	N-Ch		52	80	
		I_F = -1.7 A, di/dt = 100 A/μs	P-Ch		50	80	

* Pulse test; pulse width ≤300 μs, duty cycle≤2%.